



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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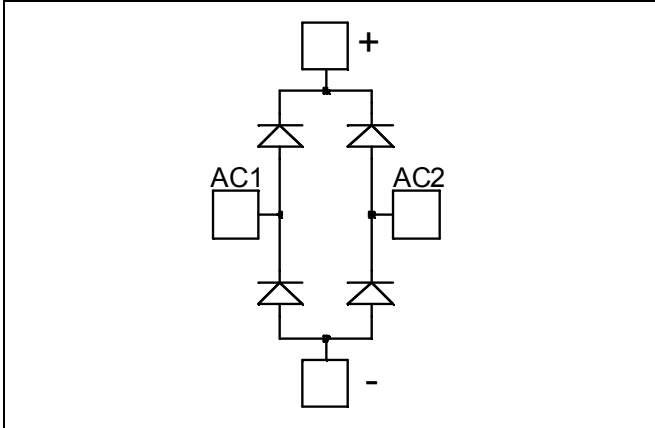
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Diode Full Bridge Power Module

$V_{RRM} = 1200V$
 $I_C = 100A @ T_c = 60^\circ C$

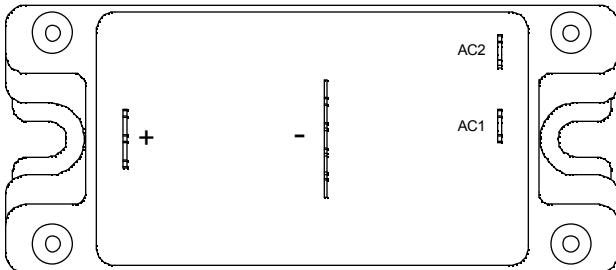


Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V_R	Maximum DC reverse Voltage	1200	V	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	$T_C = 25^\circ C$	A
			$T_C = 60^\circ C$	
$I_{F(RMS)}$	RMS Forward Current	Duty cycle = 50%	$T_C = 45^\circ C$	
I_{FSM}	Non-Repetitive Forward Surge Current	8.3ms	$T_C = 45^\circ C$	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_F	Diode Forward Voltage	$I_F = 100\text{A}$			2.4	3	V
		$I_F = 150\text{A}$			2.7		
		$I_F = 100\text{A}$	$T_j = 125^\circ\text{C}$		1.8		
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
C_T	Junction Capacitance	$V_R = 1200\text{V}$			110		pF

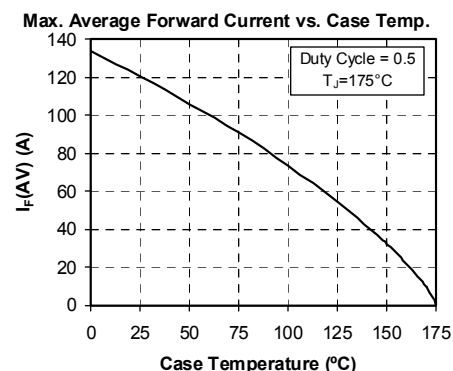
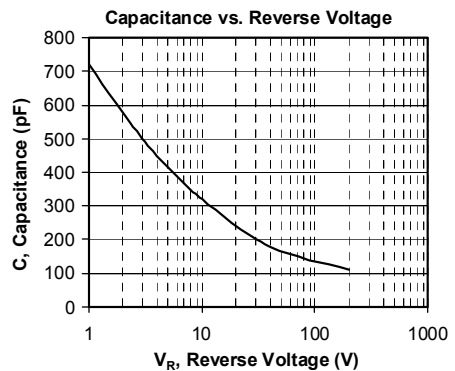
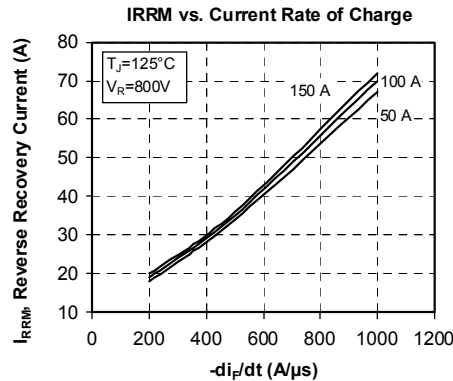
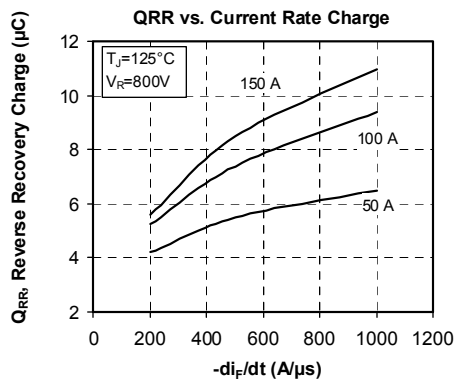
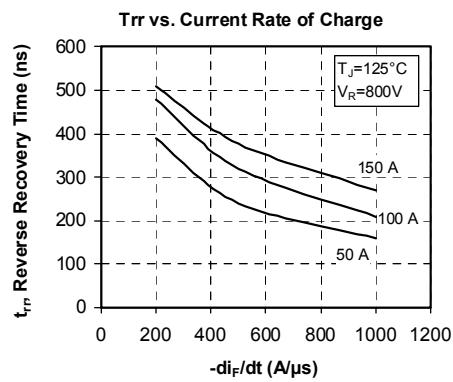
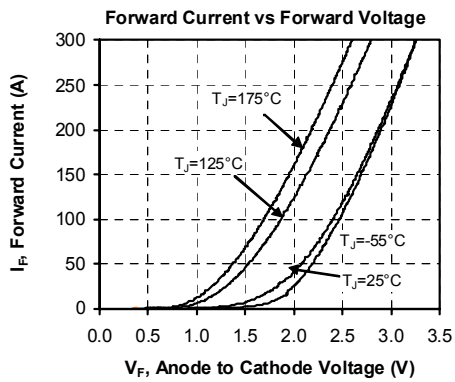
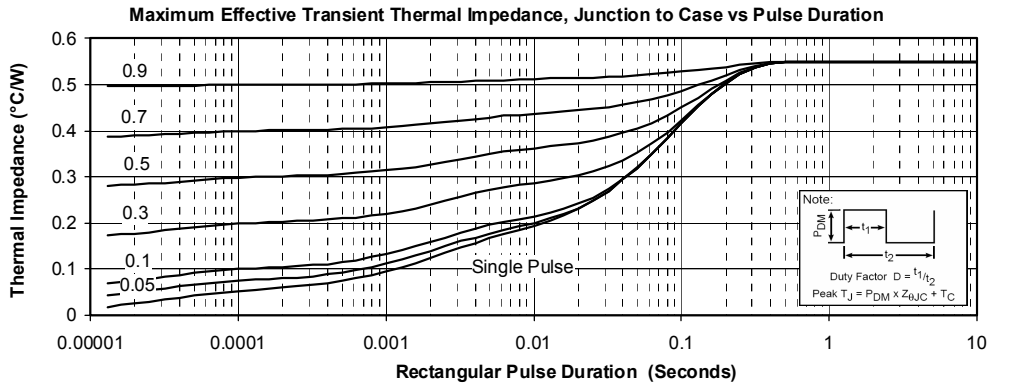
Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, V_R = 30\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		45		ns
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		385		ns
			$T_j = 125^\circ\text{C}$		480		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		1055		nC
			$T_j = 125^\circ\text{C}$		5240		
I_{RRM}	Reverse Recovery Current		$T_j = 25^\circ\text{C}$		6		A
			$T_j = 125^\circ\text{C}$		19		
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 800\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		210		ns
Q_{rr}	Reverse Recovery Charge				9.4		μC
I_{RRM}	Reverse Recovery Current				70		A

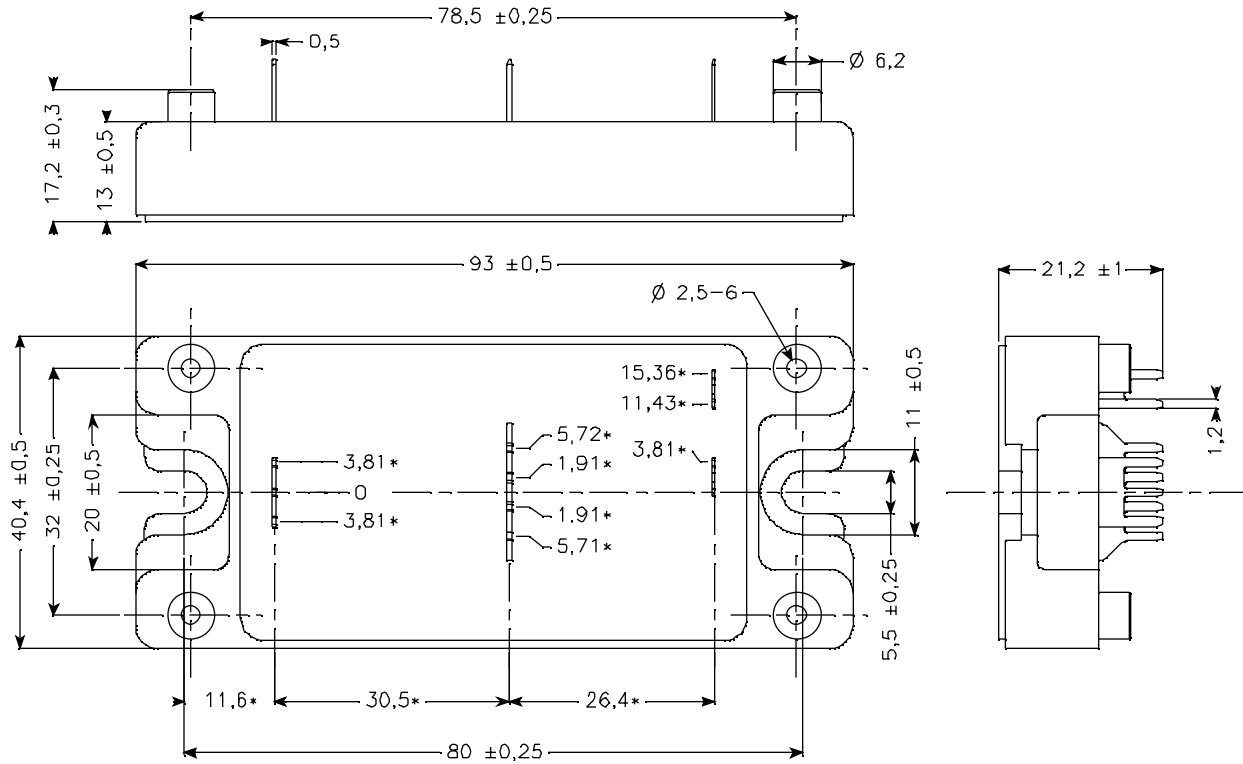
Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R_{thJC}	Junction to Case Thermal Resistance					0.55	$^\circ\text{C}/\text{W}$
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{iso} < 1\text{mA}$, 50/60Hz			2500			V
T_j	Operating junction temperature range			-40		175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

Typical Performance Curve



SP4 Package outline (dimensions in mm)



ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS : $\boxed{\varnothing \varnothing 1}$

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.